NB6L11

2.5V/3.3V Multilevel Input to Differential LVPECL/LVNECL 1:2 Clock or Data Fanout Buffer/Translator

The NB6L11 is an enhanced differential 1:2 clock or data fanout buffer/translator. The device has the same pinout and is functionally equivalent to the LVEL11, EP11, LVEP11 devices. Moreover, the device is optimized for the systems that require LOW skew, LOW jitter and LOW power consumption.

Differential input can be configured to accept single−ended signal by applying an external reference voltage to unused complimentary input pin. Input accept LVNECL, LVPECL, LVTTL, LVCMOS, CML, or LVDS. The outputs are 800 mV ECL signals.

- Maximum Input Clock Frequency ≥ 6 GHz Typical
- Maximum Input Data Rate ≥ 6 Gb/s Typical
- Low 14 mA Typical Power Supply Current
- 150 ps Typical Propagation Delay
- 5 ps Typical Within Device Skew
- 75 ps Typical Rise/Fall Times
- PECL Mode Operating Range: V_{CC} = 2.375 V to 3.465 V with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = −2.375 V to −3.465 V
- Open Input Default State
- Q Outputs Will Default LOW with Inputs Open or at V_{EE}
- LVDS, LVPECL, LVNECL, LCMOS, LVTTL and CML Input Compatible

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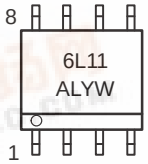
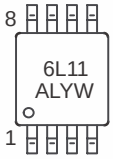
MARKING DIAGRAMS*

SO−8
D SUFFIX
CASE 751



TSSOP−8
DT SUFFIX
CASE 948R



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
NB6L11D	SO−8	98 Units/Rail
NB6L11DR2	SO−8	2500/ Tape & Reel
NB6L11DT**	TSSOP−8	100 Units/Rail
NB6L11DTR2**	TSSOP−8	2500/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
**Future Product − Contact factory for availability.

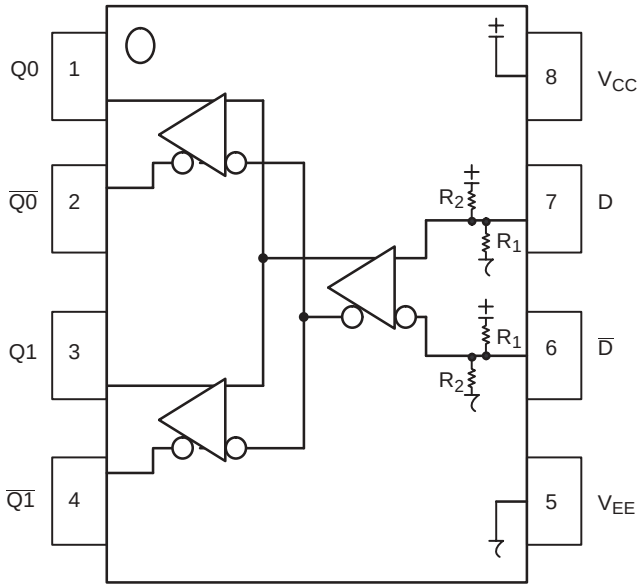


Figure 1. Pinout (Top View) **and Logic Diagram**

Table 1. PIN DESCRIPTION

Pin	Name	I/O	Default State	Description
1	Q0	ECL Output	−	Non−inverted differential clock/data output 0. Typically terminated with 50 Ω Resistor to $V_{TT} = V_{CC} - 2$ V.
2	$\overline{Q0}$	ECL Output	−	Inverted differential clock/data output 0. Typically terminated with 50 Ω resistor to $V_{TT} = V_{CC} - 2$ V.
3	Q1	ECL Output	−	Non−inverted differential clock/data output 1. Typically terminated with 50 Ω resistor to $V_{TT} = V_{CC} - 2$ V.
4	$\overline{Q1}$	ECL Output	−	Inverted differential clock/data output 1. Typically terminated with 50 Ω resistor to $V_{TT} = V_{CC} - 2$ V.
5	V_{EE}	−	−	Negative power supply voltage
6	$\overline{D}$	LVDS, CML, LVPECL, LVNECL, LVCMOS, LVTTL Input	HIGH	Inverted differential clock/data input. Internal 37.5 kΩ to V_{CC} and 75 kΩ to V_{EE}.
7	D	LVDS, CML, LVPECL, LVNECL, LVCMOS, LVTTL Input	LOW	Non−inverted differential clock/data input. Internal 75 kΩ to V_{CC} and 37.5 kΩ to V_{EE}.
8	V_{CC}	−	−	Positive power supply voltage

Table 2. ATTRIBUTES

Characteristics		Value
Internal Input Default State Resistor	(R_1)	37.5 kΩ
Internal Input Default State Resistor	(R_2)	75 kΩ
ESD Protection	Human Body Model Machine Model Charged Device Model	> 2 kV > 100 V > 1 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in
Transistor Count		167
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	V_{EE} = 0 V		3.6	V
V_{EE}	Negative Power Supply	V_{CC} = 0 V		−3.6	V
V_I	Positive Input Voltage Negative Input Voltage	V_{EE} = 0 V V_{CC} = 0 V	$V_I \le V_{CC}$ $V_I \ge V_{EE}$	3.6 −3.6	V V
V_{INPP}	Differential Input Voltage $\lvert D - \overline{D} \rvert$	$V_{CC} - V_{EE} \ge 2.8$ V $V_{CC} - V_{EE} < 2.8$ V		2.8 $\lvert V_{CC} - V_{EE} \rvert$	V
I_{out}	Output Current	Continuous Surge		25 50	mA mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	SOIC−8 SOIC−8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	SOIC−8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction−to−Ambient)	0 lfpm 500 lfpm	TSSOP−8 TSSOP−8	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction−to−Case)	Standard Board	TSSOP−8	41 to 44	°C/W
T_{sol}	Wave Solder	< 2 to 3 sec @ 248°C		265	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

Table 4. DC CHARACTERISTICS, PECL V_{CC} = 2.5 V, V_{EE} = 0 V (Note 4)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Negative Power Supply Current (Note 5)	5	14	20	5	14	20	5	14	20	mA
V_{OH}	Output HIGH Voltage (Note 6)	1350	1450	1550	1400	1500	1600	1450	1550	1650	mV
V_{OL}	Output LOW Voltage (Note 6)	630	750	870	680	800	920	730	850	970	mV
DIFFERENTIAL INPUT DRIVEN SINGLE−ENDED (Figures 10, 12)											
V_{th}	Input Threshold Reference Voltage Range (Note 2)	1125		V_{CC} −75	1125		V_{CC} −75	1125		V_{CC} −75	mV
V_{IH}	Single−Ended Input HIGH Voltage	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	mV
V_{IL}	Single−Ended Input LOW Voltage	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	mV
DIFFERENTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11, 13)											
V_{IHD}	Differential Input HIGH Voltage	1200		V_{CC}	1200		V_{CC}	1200		V_{CC}	mV
V_{ILD}	Differential Input LOW Voltage	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	mV
V_{CMR}	Input Common Mode Range (Differential Cross−Point Voltage) (Note 3)	1163		V_{CC} −38	1163		V_{CC} −38	1163		V_{CC} −38	mV
V_{ID}	Differential Input Voltage (V_{IHD} − V_{ILD})	75		2500	75		2500	75		2500	mV
I_{IH}	Input HIGH Current D $\overline{D}$		50 10	150 150		50 10	150 150		50 10	150 150	μA
I_{IL}	Input LOW Current D $\overline{D}$	−150 −150	−5 −30		−150 −150	−5 −30		−150 −150	−5 −30		μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

2. V_{th} is applied to the complementary input when operating in single−ended mode.
3. V_{CMR} minimum varies 1:1 with V_{EE}, V_{CMR} maximum varies 1:1 with V_{CC}.
4. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.125 V to −1.3 V.
5. All input and output pins left open.
6. All loading with 50 Ω to V_{CC} − 2.0 V.

Table 5. DC CHARACTERISTICS, PECL V_{CC} = 3.3 V, V_{EE} = 0 V (Note 9)

		−40°C			25°C			85°C			
Symbol	**Characteristic**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
I_{EE}	Negative Power Supply Current (Note 10)	5	14	20	5	14	20	5	14	20	mA
V_{OH}	Output HIGH Voltage (Note 11)	2150	2250	2350	2200	2300	2400	2250	2350	2450	mV
V_{OL}	Output LOW Voltage (Note 11)	1430	1550	1670	1480	1600	1720	1530	1650	1770	mV
DIFFERENTIAL INPUT DRIVEN SINGLE−ENDED (Figures 10, 12)											
V_{th}	Input Threshold Reference Voltage Range (Note 7)	1125		V_{CC} −75	1125		V_{CC} −75	1125		V_{CC} −75	mV
V_{IH}	Single−Ended Input HIGH Voltage	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	mV
V_{IL}	Single−Ended Input LOW Voltage	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	mV
DIFFERENTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11, 13)											
V_{IHD}	Differential Input HIGH Voltage	1200		V_{CC}	1200		V_{CC}	1200		V_{CC}	mV
V_{ILD}	Differential Input LOW Voltage	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	mV
V_{CMR}	Input Common Mode Range (Differential Cross−Point Voltage) (Note 8)	1163		V_{CC} −38	1163		V_{CC} −38	1163		V_{CC} −38	mV
V_{ID}	Differential Input Voltage (V_{IHD} − V_{ILD})	75		2500	75		2500	75		2500	mV
I_{IH}	Input HIGH Current D $\overline{D}$		50 10	150 150		50 10	150 150		50 10	150 150	μA
I_{IL}	Input LOW Current D $\overline{D}$	−150 −150	−5 −30		−150 −150	−5 −30		−150 −150	−5 −30		μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

7. V_{th} is applied to the complementary input when operating in single−ended mode.
8. V_{CMR} minimum varies 1:1 with V_{EE}, V_{CMR} maximum varies 1:1 with V_{CC}.
9. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to −2.2 V.
10. All input and output pins left open.
11. All loading with 50 Ω to V_{CC} − 2.0 V.

Table 6. DC CHARACTERISTICS, NECL V_{CC} = 0 V; V_{EE} = −3.465 V to −2.375 V (Note 14)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Negative Power Supply Current (Note 15)	5	14	20	5	14	20	5	14	20	mA
V_{OH}	Output HIGH Voltage (Note 16)	−1150	−1050	−950	−1100	−1000	−900	−1050	−950	−850	mV
V_{OL}	Output LOW Voltage (Note 16)	−1870	−1750	−1630	−1820	−1700	−1580	−1770	−1650	−1530	mV
DIFFERENTIAL INPUT DRIVEN SINGLE−ENDED (Figures 10, 12)											
V_{th}	Input Threshold Reference Voltage Range (Note 12)	V_{EE} +1125		V_{CC} −75	V_{EE} +1125		V_{CC} −75	V_{EE} +1125		V_{CC} −75	mV
V_{IH}	Single−Ended Input HIGH Voltage	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	V_{th} +75		V_{CC}	mV
V_{IL}	Single−Ended Input LOW Voltage	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	V_{EE}		V_{th} −75	mV
DIFFERENTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11, 13)											
V_{IHD}	Differential Input HIGH Voltage	V_{EE} +1200		V_{CC}	V_{EE} +1200		V_{CC}	V_{EE} +1200		V_{CC}	mV
V_{ILD}	Differential Input LOW Voltage	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	V_{EE}		V_{CC} −75	mV
V_{CMR}	Input Common Mode Range (Differential Cross−Point Voltage) (Note 13)	V_{EE} +1163		V_{CC} −38	V_{EE} +1163		V_{CC} −38	V_{EE} +1163		V_{CC} −38	mV
V_{ID}	Differential Input Voltage (V_{IHD} − V_{ILD})	75		2500	75		2500	75		2500	mV
I_{IH}	Input HIGH Current D $\overline{D}$		50 10	150 150		50 10	150 150		50 10	150 150	μA
I_{IL}	Input LOW Current D $\overline{D}$	−150 −150	−5 −30		−150 −150	−5 −30		−150 −150	−5 −30		μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

12. V_{th} is applied to the complementary input when operating in single−ended mode.
13. V_{CMR} minimum varies 1:1 with V_{EE}, V_{CMR} maximum varies 1:1 with V_{CC}
14. Input and output parameters vary 1:1 with V_{CC}.
15. Input and output pins left open.
16. All loading with 50 Ω to V_{CC} − 2.0 V.

Table 7. AC CHARACTERISTICS V_{CC} = 0 V; V_{EE} = −3.465 V to −2.375 V or V_{CC} = 2.375 V to 3.465 V; V_{EE} = 0 V (Note 17)

Symbol	Characteristic		−40°C			25°C			85°C			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OUTPP}	Output Voltage Amplitude (See Figures 2 & 3)	$f_{in} \le 3$ GHz $f_{in} \le 6$ GHz	480 270	700 300		480 270	700 300		480 270	700 300		mV
t_{PLH}, t_{PHL}	Propagation Delay to Output Differential @ 1 GHz	D to Q, $\overline{Q}$	110	150	190	110	150	200	120	160	220	ps
t_{SKEW}	Duty Cycle Skew Within Device Skew Device−to−Device Skew	(Note 18)		2 5 15	10 15 60		2 5 15	10 15 60		2 5 15	10 15 60	ps
t_{JITTER}	RMS Random Clock Jitter (Note 19) Peak−to−Peak Data Dependent Jitter (Note 20)	$f_{in} \le 6$ GHz $f_{in} \le 6$ Gb/s		0.2 2	1 12		0.2 2	1 12		0.2 2	1 12	ps
V_{INPP}	Input Voltage Swing / Sensitivity (Differential Configuration) (Note 21)		75	700	2500	75	700	2500	75	700	2500	mV
t_r t_f	Output Rise/Fall Times @ 1 GHz (20% − 80%)	Q, $\overline{Q}$	30	75	120	30	75	120	30	75	120	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

17. Measured using a 800 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} − 2.0 V. Input edge rates 40 ps (20% − 80%).
18. See Figure 9 $t_{skew} = |t_{PLH} - t_{PHL}|$ for a nominal 50% differential clock input waveform. Skew is measured between outputs under identical transitions and conditions @ 1 GHz.
19. Additive RMS jitter with 50% duty cycle clock signal at 6 GHz.
20. Additive Peak−to−Peak data dependent jitter with NRZ PRBS 2^{23}−1 data rate at 6 Gb/s.
21. $V_{INPP(max)}$ cannot exceed $V_{CC} - V_{EE}$ (applicable only when $V_{CC} - V_{EE} < 2500$ mV). Input voltage swing is a single−ended measurement operating in differential mode

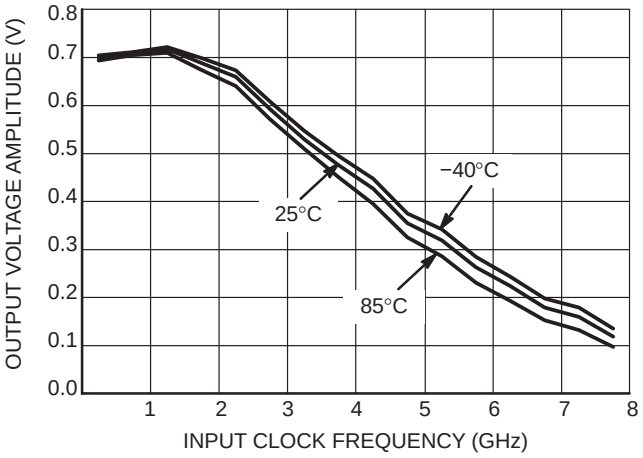


Figure 2. Output Voltage Amplitude (V_{OUTPP}) versus Input Clock Frequency (f_{IN}) and Temperature at $V_{CC} - V_{EE}$ = 3.3 V

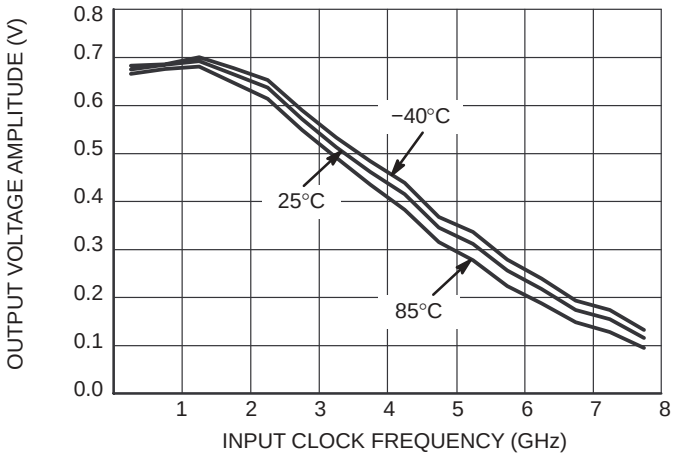


Figure 3. Output Voltage Amplitude (V_{OUTPP}) versus Input Clock Frequency (f_{IN}) and Temperature at $V_{CC} - V_{EE}$ = 2.5 V

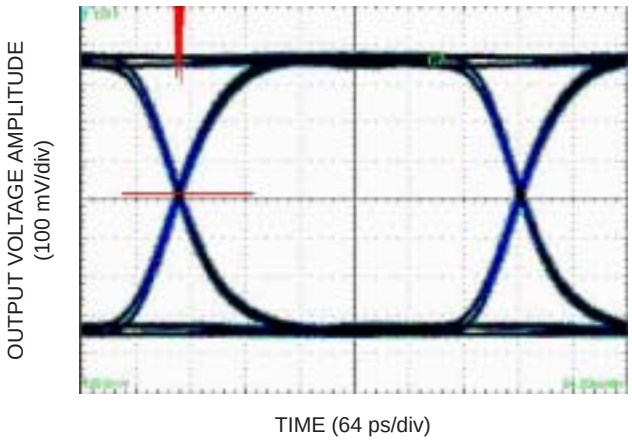


Figure 4. Typical Output Waveform at 2.488 Gb/s with PRBS 2^{23}–1 (Total System Pk−Pk Jitter is 17 ps. Device Pk−Pk Jitter Contribution is 4 ps)

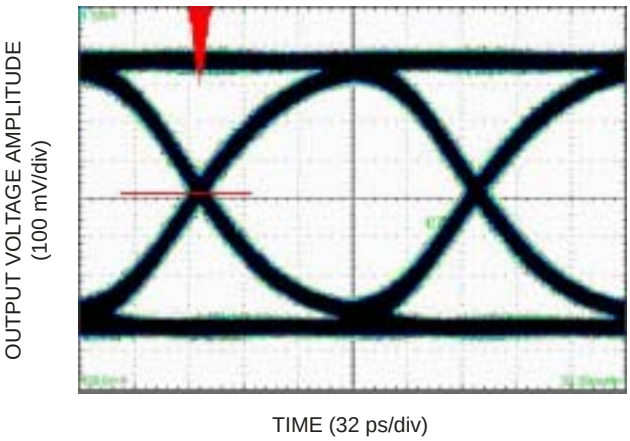


Figure 5. Typical Output Waveform at 6.125 Gb/s with PRBS 2^{23}–1 (Total System Pk−Pk Jitter is 20 ps. Device Pk−Pk Jitter Contribution is 5 ps)

NOTE: V_{CC} − V_{EE} = 3.3 V; V_{IN} = 700 mV; T_A = 25°C.

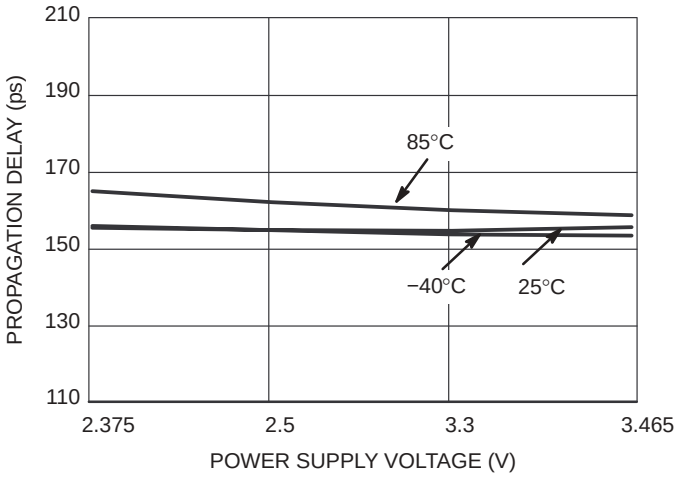


Figure 6. Propagation Delay versus Power Supply Voltage and Temperature

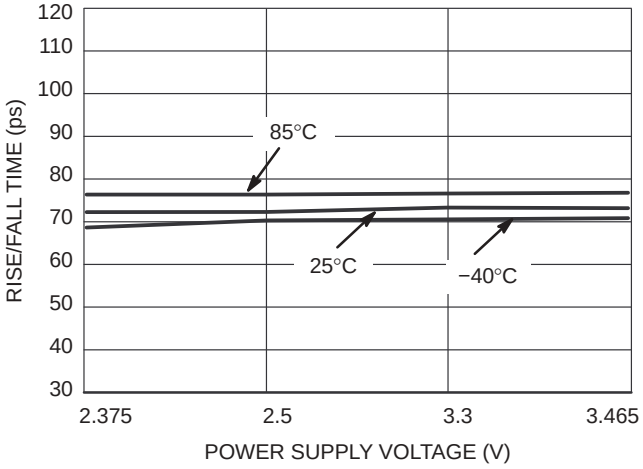


Figure 7. Rise/Fall Time versus Power Supply Voltage and Temperature

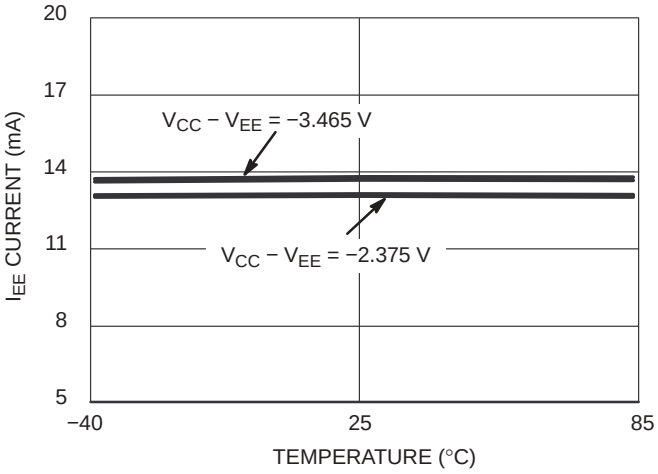


Figure 8. I_{EE} Current versus Temperature and Power Supply Voltage

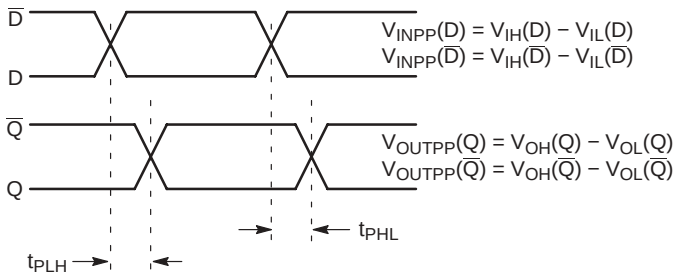


Figure 9. AC Reference Measurement

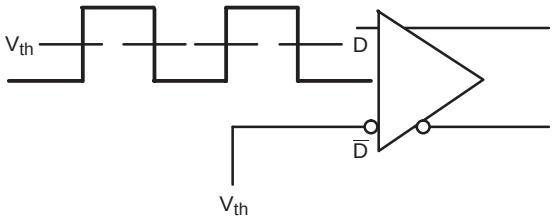


Figure 10. Differential Input Driven Single−Ended

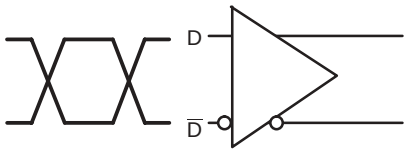


Figure 11. Differential Inputs Driven Differentially

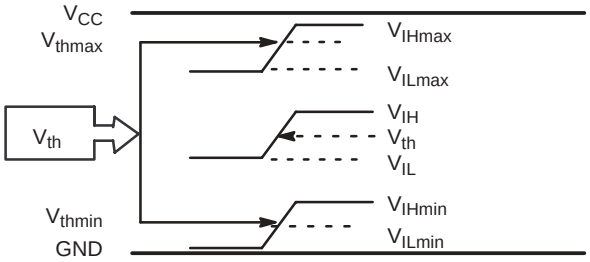


Figure 12. V_{th} Diagram

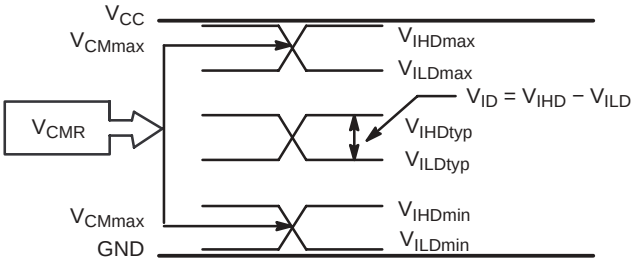


Figure 13. V_{CMR} Diagram

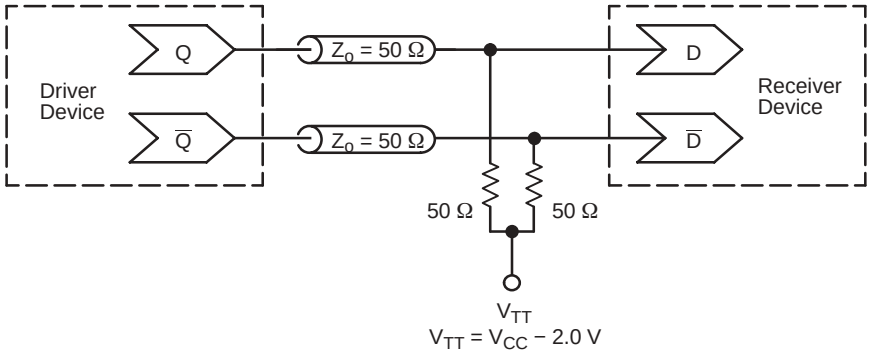


Figure 14. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D − Termination of ECL Logic Devices.)

Resource Reference of Application Notes

AN1405 − ECL Clock Distribution Techniques

AN1568 − Interfacing Between LVDS and ECL

AN1650 − Using Wire−OR Ties in ECLinPS Designs

AN1672 − The ECL Translator Guide

AND8001 − Odd Number Counters Design

AND8002 − Marking and Date Codes

AND8003 − Storage and Handling of Drypack Surface Mount Device

AND8020 − Termination of ECL Logic Devices

AND8072 − Thermal Analysis and Reliability of Wire Bonded ECL

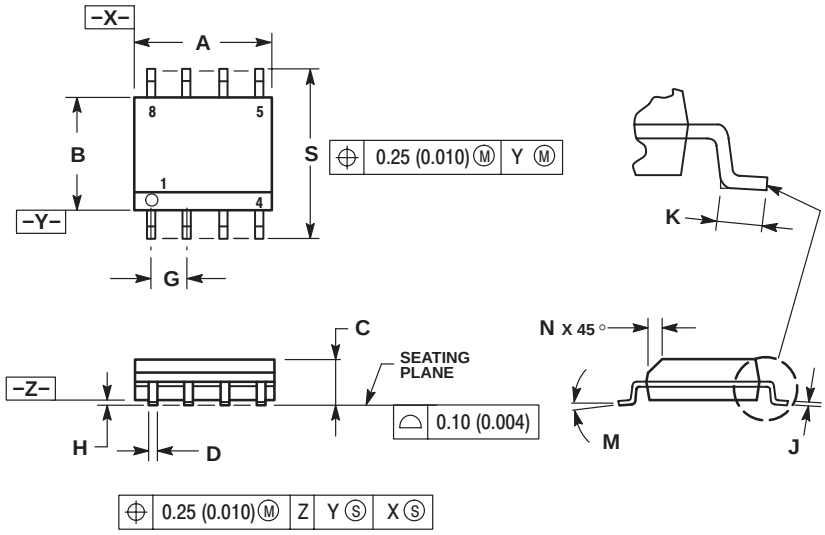
AND8066 − Interfacing with ECLinPS

AND8090 − AC Characteristics of ECL Devices

For an updated list of Application Notes, please see our website at http://onsemi.com.

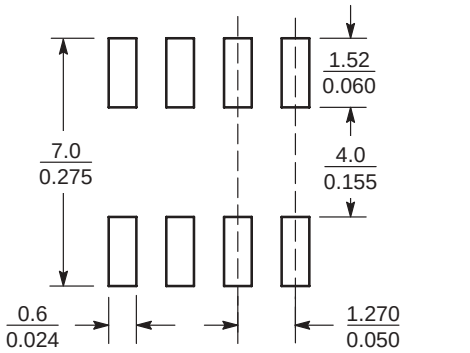
PACKAGE DIMENSIONS

SOIC−8
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751−07
ISSUE AB



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244



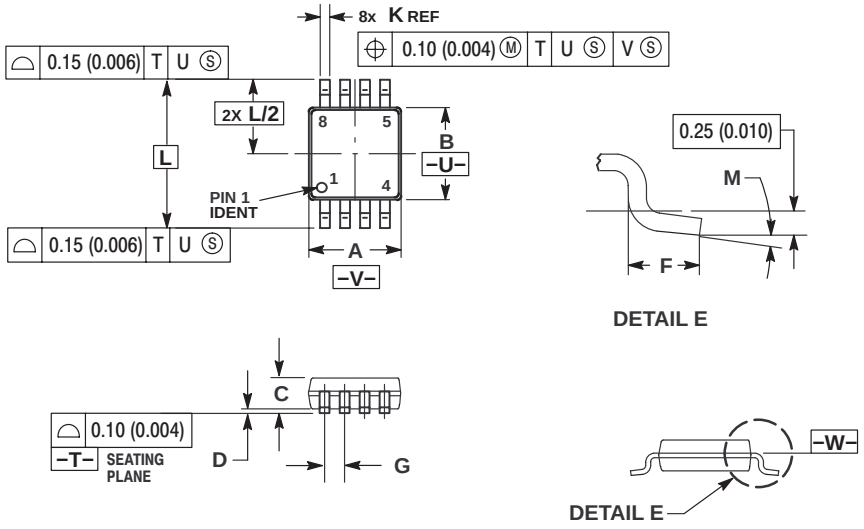
SCALE 6:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

SO−8

NB6L11

PACKAGE DIMENSIONS

TSSOP−8
DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948R−02
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0 °	6 °	0 °	6 °

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